

Abstract of the Disclosure

A Schottky diode is fabricated by a sequence of fabrication by a sequence of fabrication steps. An active region of a semiconductor substrate is defined in which a Schottky diode is fabricated. At least first and second layers of insulating material are applied over the active area. A first layer of insulating material, having a first etching rate, is applied over the active area. A second layer of insulating material having a second, greater, etch rate is applied over the first layer of insulating material to a thickness that is about twice the thickness of the first layer of insulating material. The insulating material is patterned and a window is etched through the layers of insulating material to the semiconductor substrate. Metal is applied and unwanted metal is etched away leaving metal in the window forming a Schottky contact therein. One or more barrier layers may be employed.